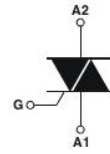


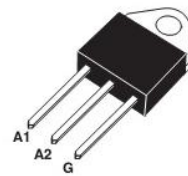
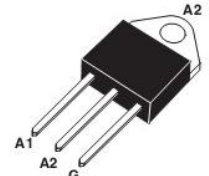
Features:

- * NPNPN Bi-direction Triac
- * Back multilayer metal electrode
- * High temperature reliability
- * Glass Passivated junction chips



Application:

Power tool ,moto speed controller, Vacuum cleaner,heating temperature controller, Solid state relay and phase control circuits.


TOP3

TOP3

Symbol	Absolute maximum ratings Parameters			Value	Unit
$I_{T(RMS)}$	RMS on-state current	BTA BTB	$T_c=80^{\circ}C$ $T_c=90^{\circ}C$	26	A
I_{TSM}	Non repetitive surge peak on-state current	F=50HZ	t=20ms	260	A
I^2t	I^2t value for fusing		tp=10ms	340	A ² S
di/dt	Critical rate of rise of on-state current		$T_j=125^{\circ}C$	50	A/us
V_{DRM}/V_{RRM}	Non repetitive surge peak off-state voltage		$T_j=25^{\circ}C$	600	V
I_{GM}	Peak gate current	tp=20us	$T_j=125^{\circ}C$	4	A
$P_{G(AV)}$	Average gate power dissipation		$T_j=125^{\circ}C$	1	W
Tstg Tj	Storage junction temperature range Operating junction temperature range			-40~+150 -40~+125	$^{\circ}C$

Electrical Characteristics(3Q) (Tj=25 °C, unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
I _{GT}	V _D =12V R _L =100Ω	I II III	MAX	50	mA
V _{GT}			MAX	1.5	V
V _{GD}	Tj=125°C		MIN	0.2	V
I _H	I _T =0.5A		MAX	60	mA
I _L	I _G =1.2I _{GT}		MAX	60	mA
				100	
dv/dt	V _D =2/3V _{DRM} Tj=125°C		MIN	500	V/us
(dv/dt) _c	Tj=125°C		MIN	10	V/us

Static Characteristics

Symbol	Test Condition			Value	Unit
V _{TM}	I _{TM} =50A		Tj=25°C MAX	1.50	V
V _{T0}	Threshold voltage		Tj=125°C MAX	0.85	V
R _d	Dynamic resistance		Tj=125°C MAX	9.2	mΩ
I _{DRM} I _{RDM}	V _{DRM} = V _{DRM}		Tj=25°C MAX	10	uA
			Tj=125°C	2	mA
R _{th(j-c)}	Junction to case (AC)		0.9		°C/W
			0.6		

TO-3P Dimensions
Unit: mm (± 0.1)
